SURFACE MOUNT DISPLAY

Part Number: KCSA56-107-B-26

Super Bright Yellow

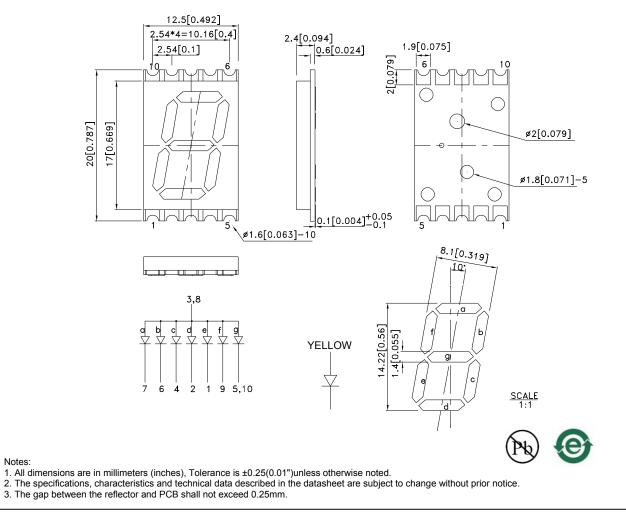
Features

- 0.56 inch digit height.
- Low current operation.
- Excellent character appearance.
- Mechanically rugged.
- Gray face, white segment.
- Package: 400pcs/ reel.
- Moisture sensitivity level : level 2a.
- RoHS compliant.

Description

The Super Bright Yellow device is made with AlGaInP (on GaAs substrate) light emitting diode chip.

Package Dimensions& Internal Circuit Diagram



SPEC NO: DSAN0227 APPROVED: WYNEC REV NO: V.2A CHECKED: Joe Lee DATE: JUN/28/2013 DRAWN: Q.M.Chen PAGE: 1 OF 5 ERP: 1351000711

Selection Guide									
Part No.	Dice	Lens Type	lv (ucd) [1] @ 10mA		Description				
			Min.	Тур.	-				
KCSA56-107-B-26	Super Bright Yellow (AlGaInP)	White Diffused	52000	117000	Common Anode				
			*21000	*38000	Common Anode				

Note:

Luminous intensity/ luminous Flux: +/-15%.
* Luminous intensity value is traceable to the CIE127-2007 compliant national standards.

Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Тур.	Max.	Units	Test Conditions
λpeak	Peak Wavelength	Super Bright Yellow	590		nm	IF=20mA
λD [1]	Dominant Wavelength	Super Bright Yellow	590		nm	IF=20mA
Δλ1/2	Spectral Line Half-width	Super Bright Yellow	20		nm	IF=20mA
С	Capacitance	Super Bright Yellow	20		pF	VF=0V;f=1MHz
VF [2]	Forward Voltage	Super Bright Yellow	2.0	2.5	V	IF=20mA
IR	Reverse Current	Super Bright Yellow		10	uA	VR=5V

Notes:

1.Wavelength: +/-1nm. 2. Forward Voltage: +/-0.1V.

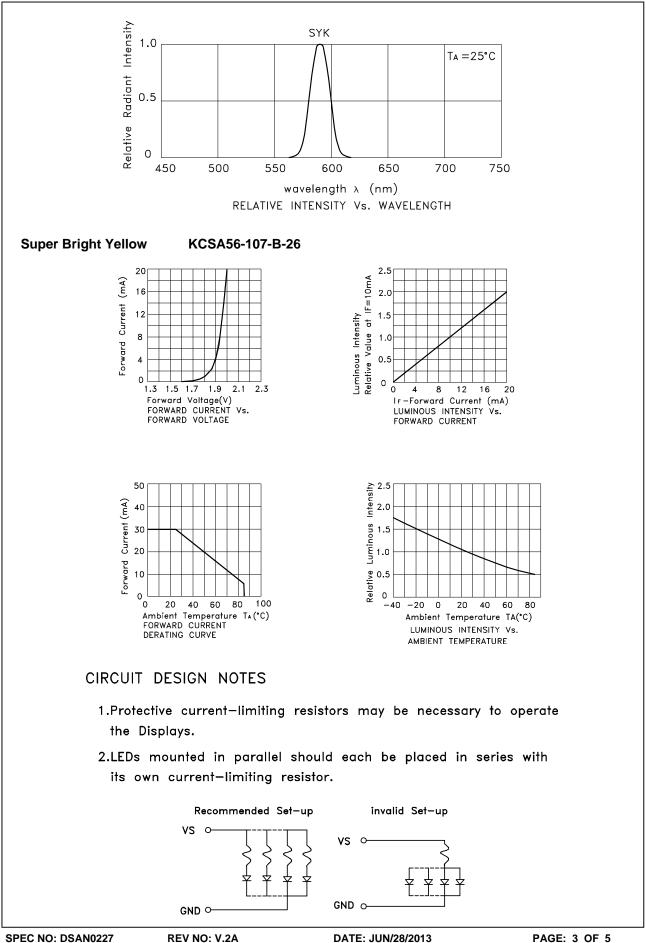
3. Wavelength value is traceable to the CIE127-2007 compliant national standards.

Absolute Maximum Ratings at TA=25°C

Parameter	Super Bright Yellow	Units	
Power dissipation	75	mW	
DC Forward Current	30	mA	
Peak Forward Current [1]	175	mA	
Reverse Voltage	5	V	
Operating / Storage Temperature	-40°C To +85°C		

Note:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.

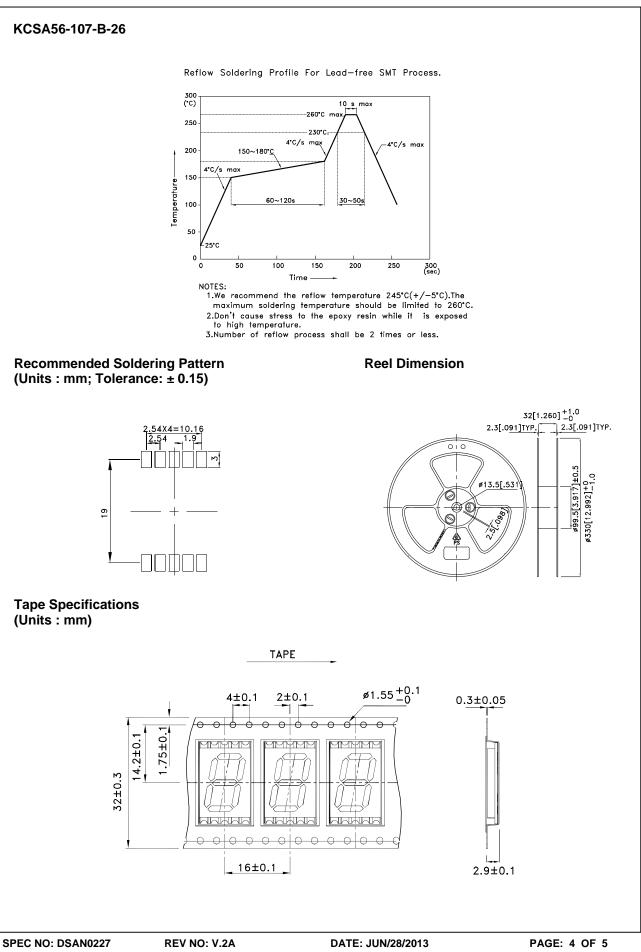


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